2.5 V 1:2 AnyLevel[™] Input to LVDS Fanout Buffer / Translator

The NB6L11S is a differential 1:2 clock or data receiver and will accept AnyLevel™ input signals: LVPECL, CML, LVCMOS, LVTTL, or LVDS. These signals will be translated to LVDS and two identical copies of Clock or Data will be distributed, operating up to 2.0 GHz or 2.5 Gb/s, respectively. As such, the NB6L11S is ideal for SONET, GigE, Fiber Channel, Backplane and other Clock or Data distribution applications.

The NB6L11S has a wide input common mode range from GND + 50 mV to V_{CC} – 50 mV. Combined with the 50 Ω internal termination resistors at the inputs, the NB6L11S is ideal for translating a variety of differential or single–ended Clock or Data signals to 350 mV typical LVDS output levels.

The NB6L11S is the 2.5 V version of the NB6N11S and is offered in a small 3 mm X 3 mm 16–QFN package. Application notes, models, and support documentation are available at www.onsemi.com.

Features

- Input Clock Frequency > 2.0 GHz
- Input Data Rate > 2.5 Gb/s
- RMS Clock Jitter -0.5 ps, Typical
- 622 Mb/s Data Dependent Jitter 6 ps, Typical
- 380 ps Typical Propagation Delay
- 120 ps Typical Rise and Fall Times
- Single Power Supply; $V_{CC} = 2.5 \text{ V} \pm 5\%$
- These are Pb-Free Devices

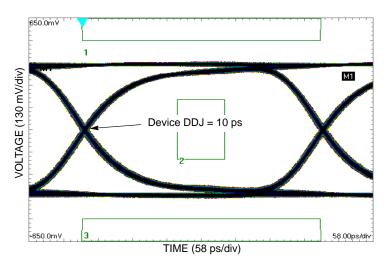


Figure 2. Typical Output Waveform at 2.488 Gb/s with PRBS 2^{23-1} (V_{INPP} = 400 mV; Input Signal DDJ = 14 ps)



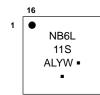
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MARKING DIAGRAM*



QFN-16 MN SUFFIX CASE 485G



A = Assembly Location

L = Wafer Lot Y = Year W = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)
*For additional marking information, refer to
Application Note AND8002/D.

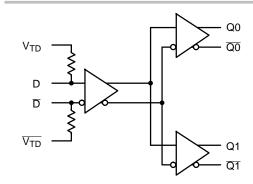


Figure 1. Logic Diagram

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 10 of this data sheet.

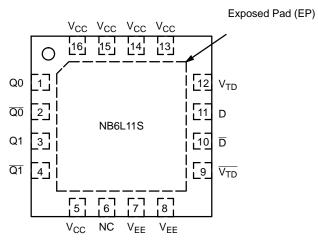


Figure 3. NB6L11S Pinout, 16-pin QFN (Top View)

Table 1. PIN DESCRIPTION

| Pin | Name | I/O | Description | | | |
|-----|---------------------|-------------------------------------|---|--|--|--|
| 1 | Q0 | LVDS Output | Non–inverted D output. Typically loaded with 100 Ω receiver termination resistor across differential pair. | | | |
| 2 | Q0 | LVDS Output | Inverted D output. Typically loaded with 100 Ω receiver termination resistor across differential pair. | | | |
| 3 | Q1 | LVDS Output | Non–inverted D output. Typically loaded with 100 Ω receiver termination resistor across differential pair. | | | |
| 4 | Q1 | LVDS Output | Inverted D output. Typically loaded with 100 Ω receiver termination resistor across differential pair. | | | |
| 5 | V _{CC} | - | Positive Supply Voltage. | | | |
| 6 | NC | | No Connect. | | | |
| 7 | V _{EE} | | Negative Supply Voltage. | | | |
| 8 | V _{EE} | | Negative Supply Voltage. | | | |
| 9 | $\overline{V_{TD}}$ | - | Internal 50 Ω termination pin for $\overline{\mathbb{D}}$. | | | |
| 10 | D | LVPECL, CML, LVDS, LVCMOS, LVTTL | Inverted Differential Clock/Data Input (Note 1). | | | |
| 11 | D | LVPECL, CML, LVDS, LVCMOS, LVTTL | Non-inverted Differential Clock/Data Input (Note 1). | | | |
| 12 | V_{TD} | - | Internal 50 Ω termination pin for $\overline{D}.$ | | | |
| 13 | V _{CC} | - | Positive Supply Voltage. | | | |
| 14 | V _{CC} | - | Positive Supply Voltage. | | | |
| 15 | V _{CC} | - | Positive Supply Voltage. | | | |
| 16 | V _{CC} | - | Positive Supply Voltage. | | | |
| EP | | | Exposed pad. The exposed pad (EP) on the package bottom must be attached to a heat–sinking conduit. The exposed pad may only be electrically connected to V _{EE} . | | | |

In the differential configuration when the input termination pins (V_{TD}, √(TD)) are connected to a common termination voltage or left open, and if no signal is applied on D, D input, then the device will be susceptible to self–oscillation.

Table 2. ATTRIBUTES

| Characte | Value | | | | |
|--|-----------------------------|--|--|--|--|
| ESD Protection | > 2 kV > 200 V > 1 kV | | | | |
| Moisture Sensitivity (Note 2) | Pb-Free Pkg | | | | |
| | Level 1 | | | | |
| Flammability Rating Oxygen Index | UL 94 V-0 @ 0.125 in | | | | |
| Transistor Count | 225 | | | | |
| Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test | | | | | |

^{2.} For additional information, see Application Note AND8003/D.

Table 3. MAXIMUM RATINGS

| Symbol | Parameter | Condition 1 | Condition 2 | Rating | Unit |
|-------------------|---|-------------------------|--------------------------|--------------|----------|
| V _{CC} | Positive Power Supply | GND = 0 V | | 3.8 | V |
| V _{IN} | Positive Input | GND = 0 V | $V_{IN} \leq V_{CC}$ | 3.8 | V |
| I _{IN} | Input Current Through R _T (50 Ω Resistor) | Static Surge | | 35 70 | mA mA |
| losc | Output Short Circuit Current Line-to-Line (Q to $\overline{\mathbf{Q}}$) Line-to-End (Q or $\overline{\mathbf{Q}}$ to GND) | Q or Q Q to Q to GND | Continuous Continuous | 12 24 | mA |
| T _A | Operating Temperature Range | QFN-16 | | -40 to +85 | °C |
| T _{stg} | Storage Temperature Range | | | -65 to +150 | °C |
| θ_{JA} | Thermal Resistance (Junction-to-Ambient) (Note 3) | 0 lfpm 500 lfpm | QFN-16 QFN-16 | 41.6 35.2 | °C/W |
| $\theta_{\sf JC}$ | Thermal Resistance (Junction-to-Case) | 1S2P (Note 3) | QFN-16 | 4.0 | °C/W |
| T _{sol} | Wave Solder Pb-Free | | | 265 | °C |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

3. JEDEC standard multilayer board – 1S2P (1 signal, 2 power) with 8 filled thermal vias under exposed pad.

Table 4. DC CHARACTERISTICS, CLOCK INPUTS, LVDS OUTPUTS V_{CC} = 2.375 V to 2.625 V, GND = 0 V, $T_A = -40^{\circ}C$ to $+85^{\circ}C$

| Symbol | Characteristic | | Min Typ | | Unit |
|------------------|---|-----------------------|----------|-----------------------|------|
| I _{CC} | Power Supply Current (Note 8) | | 30 | 45 | mA |
| DIFFERE | NTIAL INPUTS DRIVEN SINGLE-ENDED (Figures 15, 16, 20, and 22) | | | | |
| V _{th} | Input Threshold Reference Voltage Range (Note 7) | | GND +100 | | mV |
| V _{IH} | Single-ended Input HIGH Voltage | V _{th} + 100 | | V _{CC} | mV |
| V _{IL} | Single-ended Input LOW Voltage | GND | GND | | mV |
| DIFFERE | NTIAL INPUTS DRIVEN DIFFERENTIALLY (Figures 11, 12, 13, 14, 21, and 23) | | | | |
| V _{IHD} | Differential Input HIGH Voltage | 100 | | V _{CC} | mV |
| V _{ILD} | Differential Input LOW Voltage | | | V _{CC} – 100 | mV |
| V _{CMR} | Input Common Mode Range (Differential Configuration) | | | V _{CC} – 50 | mV |
| V _{ID} | Differential Input Voltage (V _{IHD} – V _{ILD}) | 100 | | V _{CC} – GND | mV |
| R _{TIN} | Internal Input Termination Resistor | 40 | 50 | 60 | Ω |
| LVDS OU | TPUTS (Note 4) | | | | |
| V _{OD} | Differential Output Voltage | 250 | | 450 | mV |
| ΔV_{OD} | Change in Magnitude of V _{OD} for Complementary Output States (Note 9) | 0 | 1 | 25 | mV |
| Vos | Offset Voltage (Figure 19) | 1125 | | 1375 | mV |
| ΔV_{OS} | Change in Magnitude of V _{OS} for Complementary Output States (Note 9) | 0 | 1 | 25 | mV |
| V _{OH} | Output HIGH Voltage (Note 5) | | 1425 | 1600 | mV |
| V _{OL} | Output LOW Voltage (Note 6) | 900 | 1075 | | mV |

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

- 4. LVDS outputs require 100 Ω receiver termination resistor between differential pair. See Figure 18.

- V_{OH}max = V_{OS}max + ½ V_{OD}max.
 V_{OL}max = V_{OS}min ½ V_{OD}max.
 V_{th} is applied to the complementary input when operating in single–ended mode.
 Iput termination resistor between differential pair. See Figure 10.
 V_{th} is applied to the complementary input when operating in single–ended mode.
 Ipput termination pins open, D/D at the DC level within V_{CMR} and output pins loaded with R_L = 100 Ω across differential.
- 9. Parameter guaranteed by design verification not tested in production.

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Table 5. AC CHARACTERISTICS $V_{CC} = 2.375 \text{ V}$ to 2.625 V, GND = 0 V; (Note 10)

| | | | -40°C | | 25°C | | 85°C | | | | |
|--|--|-------------------|----------------------------|--------------------------|-------------------|----------------------------|--------------------------|-------------------|----------------------------|--------------------------|------|
| Symbol | Characteristic | Min | Тур | Max | Min | Тур | Max | Min | Тур | Max | Unit |
| V _{OUTPP} | Output Voltage Amplitude (@ $V_{INPPmin}$) $f_{in} \le 1.0$ GHz (Figure 4) $f_{in} = 1.5$ GHz $f_{in} = 2.0$ GHz | 220 200 170 | 350 300 270 | | 220 200 170 | 350 300 270 | | 220 200 170 | 350 300 270 | | mV |
| f _{DATA} | Maximum Operating Data Rate | 1.5 | 2.5 | | 1.5 | 2.5 | | 1.5 | 2.5 | | Gb/s |
| t _{PLH} , t _{PHL} | Differential Input to Differential Output Propagation Delay | 250 | | 450 | 250 | 380 | 450 | 250 | | 450 | ps |
| t _{SKEW} | Duty Cycle Skew (Note 11) Within Device Skew (Note 16) Device—to—Device Skew (Note 15) | | 8 5 30 | 45 25 100 | | 8 5 30 | 45 25 100 | | 8 5 30 | 45 25 100 | ps |
| t _{JITTER} | RMS Random Clock Jitter (Note 13) $f_{in} = 1.0 \text{ GHz}$ $f_{in} = 1.5 \text{ GHz}$ Peak-to-Peak Data Dependent Jitter (Note 14) $f_{DATA} = 622 \text{ Mb/s}$ $f_{DATA} = 1.5 \text{ Gb/s}$ $f_{DATA} = 2.488 \text{ Gb/s}$ | | 0.5 0.5 6 7 10 | | | 0.5 0.5 6 7 10 | | | 0.5 0.5 6 7 10 | | ps |
| V _{INPP} | Input Voltage Swing/Sensitivity (Differential Configuration) (Note 12) | 100 | | V _{CC} - GND | 100 | | V _{CC} - GND | 100 | | V _{CC} - GND | mV |
| t _r t _f | Output Rise/Fall Times @ 250 MHz Q, Q (20% – 80%) | 70 | 120 | 170 | 70 | 120 | 170 | 70 | 120 | 170 | ps |

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

- 11. See Figure 17 differential measurement of t_{skew} = |t_{PLH} t_{PHL}| for a nominal 50% differential clock input waveform @ 250 MHz. 12. Input voltage swing is a single–ended measurement operating in differential mode. 13. RMS jitter with 50% Duty Cycle input clock signal.

- 14. Deterministic jitter with input NRZ data at PRBS 2²³–1 and K28.5.
- 15. Skew is measured between outputs under identical transition @ 250 MHz.
- 16. The worst case condition between $Q0/\overline{Q0}$ and $Q1/\overline{Q1}$ from D, \overline{D} , when both outputs have the same transition.

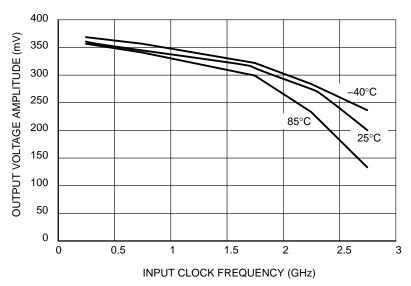


Figure 4. Output Voltage Amplitude (V_{OUTPP}) versus Input Clock Frequency (f_{in}) and Temperature (@ $V_{CC} = 2.5 \text{ V}$)

^{10.} Measured by forcing $V_{INPPmin}$ with 50% duty cycle clock source and V_{CC} – 1400 mV offset. All loading with an external R_L = 100 Ω across "D" and " \overline{D} " of the receiver. Input edge rates 150 ps (20%–80%).

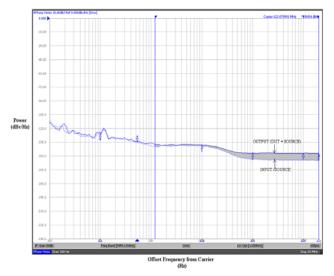


Figure 5. Typical Phase Noise Plot at f_{carrier} = 622.08 MHz

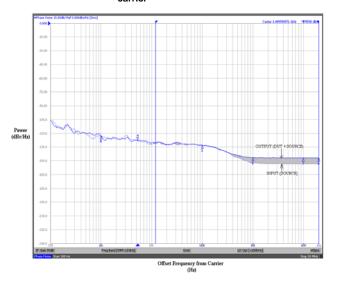


Figure 7. Typical Phase Noise Plot at $f_{carrier} = 1.5 \text{ GHz}$

The above phase noise plots captured using Agilent E5052A show additive phase noise of the NB6L11S device at frequencies 622.08 MHz, 1 GHz, 1.5 GHz and 2 GHz respectively at an operating voltage of 2.5 V in room temperature. The RMS Phase Jitter contributed by the

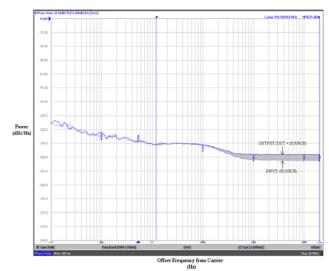


Figure 6. Typical Phase Noise Plot at $f_{carrier} = 1 \text{ GHz}$

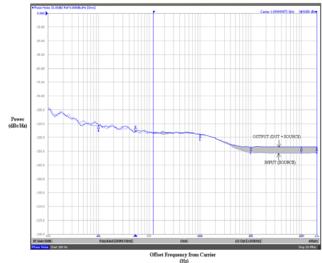


Figure 8. Typical Phase Noise Plot at f_{carrier} = 2 GHz

device (integrated between 12 kHz and 20 MHz; as shown in the shaded region of the plot) at each of the frequencies is 40 fs, 22 fs, 14 fs and 12 fs respectively. The input source used for the phase noise measurements is Agilent E8663B.

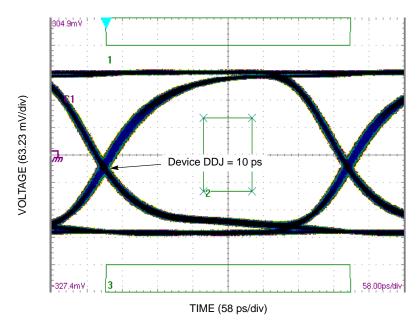


Figure 9. Typical Output Waveform at 2.488 Gb/s with PRBS 2^{23-1} and OC48 mask ($V_{INPP} = 100$ mV; Input Signal DDJ = 14 ps)

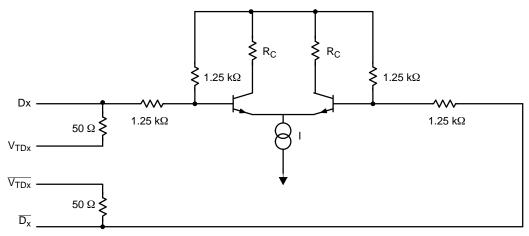


Figure 10. Input Structure

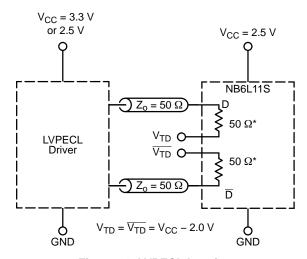


Figure 11. LVPECL Interface

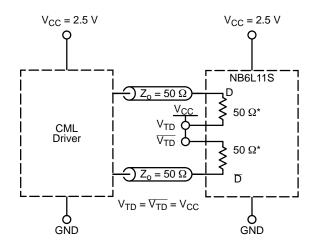


Figure 13. Standard 50 Ω Load CML Interface

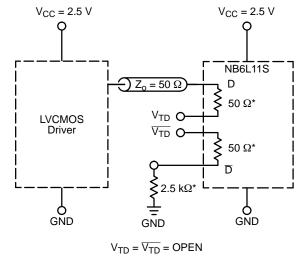


Figure 15. LVCMOS Interface

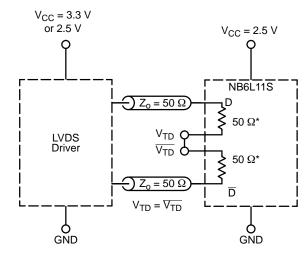


Figure 12. LVDS Interface

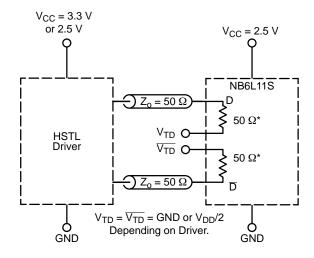


Figure 14. HSTL Interface

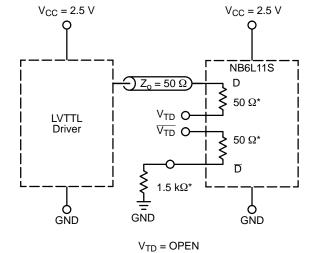


Figure 16. LVTTL Interface

*R_{TIN}, Internal Input Termination Resistor.

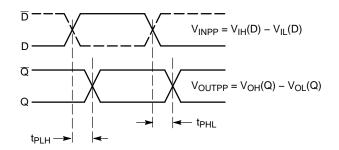


Figure 17. AC Reference Measurement

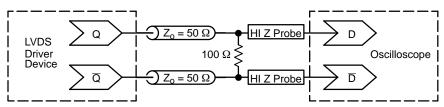


Figure 18. Typical LVDS Termination for Output Driver and Device Evaluation

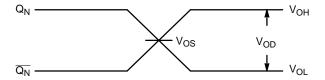


Figure 19. LVDS Output

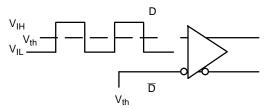
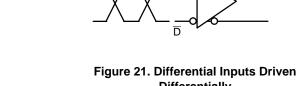


Figure 20. Differential Input Driven Single-Ended



Differentially

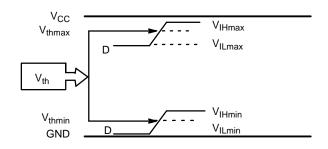


Figure 22. V_{th} Diagram

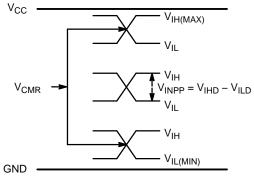


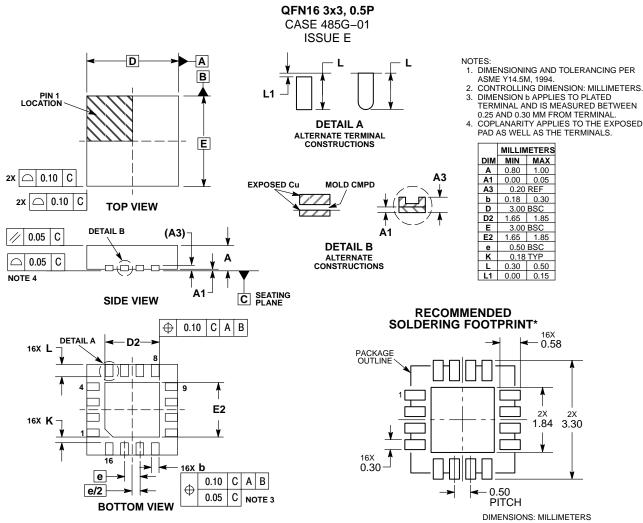
Figure 23. V_{CMR} Diagram

ORDERING INFORMATION

| Device | Package | Shipping [†] |
|--------------|-------------------------------|-----------------------|
| NB6L11SMNG | QFN-16, 3 X 3 mm (Pb-Free) | 123 Units / Rail |
| NB6L11SMNR2G | QFN-16, 3 X 3 mm (Pb-Free) | 3000 / Tape & Reel |

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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